

## 64-bit CMOS FUSE ROM

The S-2100R is a 64-bit serial CMOS FUSE ROM. It has low standby current ( $0.3\mu\text{A}$  max.,  $V_{DD}=1.5\text{V}$ ) and has a wide operating voltage range. Data can be read serially by clock pulses from address 1 to address 64. All the addresses are initialized at "H" so writing into "L" can be done only once.

### ■ Features

- Low standby current ( $0.3\mu\text{A}$  max.,  $V_{DD}=1.5\text{V}$ )
- Wide operating voltage range (1.1V to 5.5V)

### ■ Applications

- Pager ID ROM
- Cordless telephones
- Security equipment

### ■ Pin Assignment

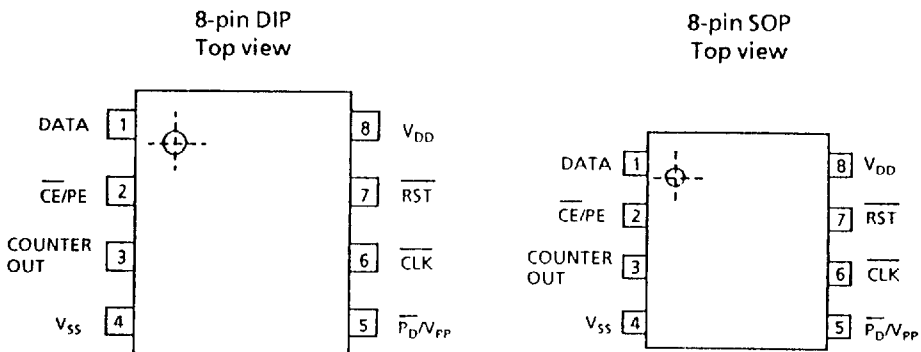


Figure 1

# S-2100R

## ■ Block Diagram

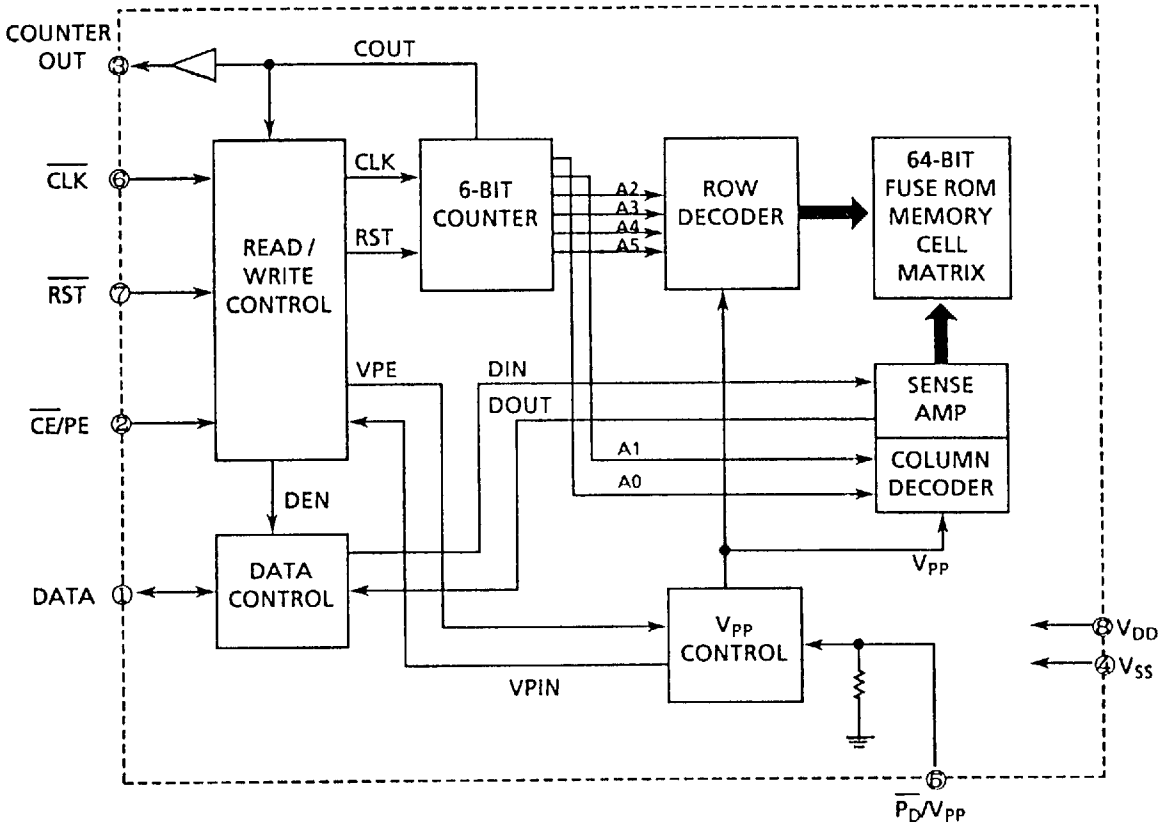


Figure 2

■ Terminal description

Table 1

Name	Symbol	Contents
Data input/output terminal	DATA	Tri-state data input/output terminal
Mode select terminal	$\overline{\text{CE/PE}}$	Mode select terminal (Refer to operation mode table.)
Counter output terminal	COUNTER OUT	6-bit counter; 64th bit detector output terminal
Negative power supply terminal	$V_{SS}$	Generally connected to GND.
Program voltage input terminal	$\overline{P_D/V_{PP}}$	Input terminal of writing voltage to FUSE memory at 21V. (Refer to operation mode table.) Built-in-pull-down resistance.
Clock input terminal	$\overline{\text{CLK}}$	Clock input terminal of 6-bit counter. Operates at the falling edge.
Reset input terminal	$\overline{\text{RST}}$	Reset input terminal of 6-bit counter. Operates at "L".
Positive power supply terminal	$V_{DD}$	Generally connected to + 1.1 to + 5.5V.

■ Mode Table

Table 2

Mode \ Terminal	$\overline{\text{CE/PE}}$	$\overline{P_D/V_{PP}}$	$\overline{\text{CLK}}$	$\overline{\text{RST}}$	DATA
Read	$V_{SS}$	$V_{SS}$	Input possible	Input possible	Data output
Counter hold	$V_{DD}$	$V_{SS}$	Input impossible	Input impossible	High impedance
Program	$V_{DD}$	$V_{PP}$	Input impossible	Input impossible	Data input

# S-2100R

## Absolute Maximum Ratings

Table 3

Item	Symbol	Ratings	Unit
Power supply voltage	$V_{DD}$	-0.3 to +6.5	V
PD/ $V_{PP}$ input voltage	$V_{PP}$	-0.3 to 26	V
Input voltage	$V_{IN}$	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
output voltage	$V_{OUT}$	$V_{SS} - 0.3$ to $V_{DD} + 0.3$	V
Storage temperature under bias	$T_{bias}$	-30 to +85	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

## Recommended Operating Conditions

Table 4

Item	Symbol	Conditions	Min	Typ	Max	Unit
Power supply voltage	$V_{DD}$	$T_a = 25^\circ\text{C}$ , Read, $t_{CH} = 15 \mu\text{s}$	1.1	1.5	5.5	V
		$T_a = 25^\circ\text{C}$ , Write	4.5	5.0	5.5	V
High level input voltage	$V_{IH}$	$T_a = 25^\circ\text{C}$ , Read	$V_{DD} - 0.3$	—	$V_{DD}$	V
		$T_a = 25^\circ\text{C}$ , Write	$V_{DD} - 0.3$	—	$V_{DD}$	V
Low level input voltage	$V_{IL}$	$T_a = 25^\circ\text{C}$ , Read	-0.3	—	0.3	V
		$T_a = 25^\circ\text{C}$ , Write	-0.3	—	0.5	V
Operating temperature	$T_{opr}$		-20	—	70	°C

## DC Electrical Characteristics

Table 5

Item	Sym.	Conditions	Min.	Typ.	Max.	Unit
Operating current consumption	$I_{DDO}$	$V_{DD} = 1.5\text{V}$ , $f_{CLK} = 50\text{kHz}$	—	—	20	$\mu\text{A}$
Standby current consumption	$I_{DDs}$	$V_{DD} = 1.5\text{V}$ , $\overline{RST} = V_{DD}$ $CLK = V_{DD}$ , $\overline{CE/PE} = V_{SS}$	—	—	0.3	$\mu\text{A}$
$\overline{PD}/V_{PP}$ input voltage	$V_{PP}$		20	21	22	V
$\overline{PD}/V_{PP}$ input current	$I_{PP}$		—	—	150	mA
Output current	$I_{OH}$	$V_{DD} = 1.1$ to $5.5\text{V}$ , $V_{OH} = V_{DD} - 0.3\text{V}$	-300	—	—	$\mu\text{A}$
	$I_{OL}$	$V_{DD} = 1.1$ to $5.5\text{V}$ , $V_{OH} = 0.3\text{V}$	300	—	—	
Pull-down resistance	$R_D$	$V_{DD} = 1.5\text{V}$	0.1	0.2	0.4	M $\Omega$

■ AC Electrical Characteristics

(1) Read mode

Table 6

(Ta = 25°C, V<sub>DD</sub> = 1.5V)

Item	Symbol	Ratings			Unit
		Min.	Typ.	Max.	
$\overline{\text{RST}}$ hold time	t <sub>RH</sub>	5.0	—	—	μs
Read cycle time	t <sub>RC</sub>	2.0	—	—	μs
$\overline{\text{CLK}}$ hold time	t <sub>CH</sub>	5.0	—	—	μs
Access time	t <sub>ACC</sub>	—	—	5.0	μs
$\overline{\text{CE/PE}}$ setup time	t <sub>CES</sub>	2.0	—	—	μs
$\overline{\text{RST}}$ setup time	t <sub>RS</sub>	2.0	—	—	μs
$\overline{\text{CLK}}$ setup time	t <sub>CS</sub>	2.0	—	—	μs
$\overline{\text{CE}}$ access time	t <sub>CE</sub>	—	—	5.0	μs
Output disable time	t <sub>WZ</sub>	—	—	500	ns
$\overline{\text{CLK}}$ and $\overline{\text{RST}}$ inhibit time	t <sub>CRI</sub>	—	—	500	ns

Load 60pF

(2) Write mode

Table 7

(Ta = 25°C, V<sub>DD</sub> = 5.0V, V<sub>PP</sub> = 21V)

Item	Symbol	Ratings			Unit
		Min.	Typ.	Max.	
$\overline{\text{CE}}$ -data setup time	t <sub>CDS</sub>	0.5	—	—	μs
Data setup time	t <sub>DS</sub>	0.5	—	—	μs
Data hold time	t <sub>DH</sub>	0	—	—	μs
$\overline{\text{CE}}$ -data hold time	t <sub>CDH</sub>	2.0	—	—	μs
V <sub>PP</sub> rise time	t <sub>r</sub>	20	—	—	μs
Program pulse width	t <sub>PW</sub>	8.0	—	—	ms
V <sub>PP</sub> rise slope	ΔV <sub>PP</sub>	—	—	4	V/μs

# S-2100R

## ■ Read mode operation

By setting the  $\overline{\text{CE/PE}}$  terminal to the "L" level, the S-2100R/RF enters the read mode. (1) Next, adding an  $\overline{\text{RST}}$  pulse causes the contents of the memory bit of address 1 to be output at the DATA OUT terminal; the rising of the  $\overline{\text{RST}}$  pulse latches the data and stabilizes it. (2) Reading of addresses from 2 to 64 can be done by adding a  $\overline{\text{CLK}}$  pulse sequentially after reading address 1. (3)

As soon as address 64 has been read, the COUNTER OUT terminal outputs the "H" level. When it finishes reading address 64, it does not accept any more  $\overline{\text{CLK}}$  pulses and the counter does not operate. The data of address 64 is maintained till address 1 is read by the  $\overline{\text{RST}}$  pulse.

## ■ Counter hold mode

By setting the  $\overline{\text{CE/PE}}$  terminal to the "H" level, the S-2100R/RF enters the counter hold mode and the DATA terminal becomes high impedance. (4)

In counter hold mode, the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  pulses which fall while the  $\overline{\text{CE/PE}}$  terminal is at "H" level are recognized to be invalid and there is no change in counter and data output. When the  $\overline{\text{CE/PE}}$  terminal is set to the "L" level again, it returns to the condition in which it was before the counter hold mode was entered.

## ■ Program mode

By setting the  $\overline{\text{CE/PE}}$  terminal to the "H" level, it enters the counter hold mode and at the same time enters the program mode. (5)

Writing is done in program mode after selecting the address in read mode. (6) Select the address, and supply the "H" level to the  $\overline{\text{CE/PE}}$  terminal and the "L" level to the DATA terminal, with the writing pulse  $V_{PP}$  being supplied to the  $\overline{\text{PD}}/V_{PP}$  terminal. The "L" level can be written into the selected address only once. (7) (8)

If you continue writing from address 1 to address 64, the output of the COUNTER OUT terminal goes to "H" level, just like in the read mode, and no more  $\overline{\text{CLK}}$  pulses or writing pulses in program mode can be accepted.



## ■ Notes

- (1) When both the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  terminals are at the "H" level.
  - (2) When the  $\overline{\text{RST}}$  terminal is at the "L" level, the latch is transparent and the data is recognized by the rising of the  $\overline{\text{RST}}$  pulse.
  - (3) Data read by the  $\overline{\text{CLK}}$  pulse is latched at its rising.
  - (4) When both the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  terminals are at the "H" level.
  - (5) In program mode, operate at  $V_{DD}=5.0V$  to assure reliability of the data writing.
  - (6) The selection of addresses is possible only in read mode. Address 1 is selected by  $\overline{\text{RST}}$  pulses and writing proceeds sequentially from address 1 by  $\overline{\text{CLK}}$  pulses.
  - (7) All the memories are initially at the "H" level, so writing into "L" can be done. When data is at the "H" level, writing voltage cannot be supplied to the memory.
  - (8) Address 1 is selected again by the  $\overline{\text{RST}}$  pulse. The addresses which are not written to the "L" level are at the "H" level, so writing the "L" level in these addresses is possible.
  - (9) Input of the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  pulses is not recognized as valid unless both pulses are input at the "H" level.
  - (10) When reading of the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  pulses is finished and DATA output has been stabilized the counter hold mode is entered.
  - (11) No more  $\overline{\text{CLK}}$  or  $\overline{\text{RST}}$  pulses are accepted unless both the  $\overline{\text{CLK}}$  and  $\overline{\text{RST}}$  terminals are at the "H" level.
  - (12) If data input is changed while writing voltage is supplied, the S-2100R/RF does not accept the changed data.
- \* Memory should not be accessed for at least  $10\mu s$  after voltage is supplied and goes to  $V_{DD}$ .

■ Dimensions

1. S-2100R (8-pin DIP)

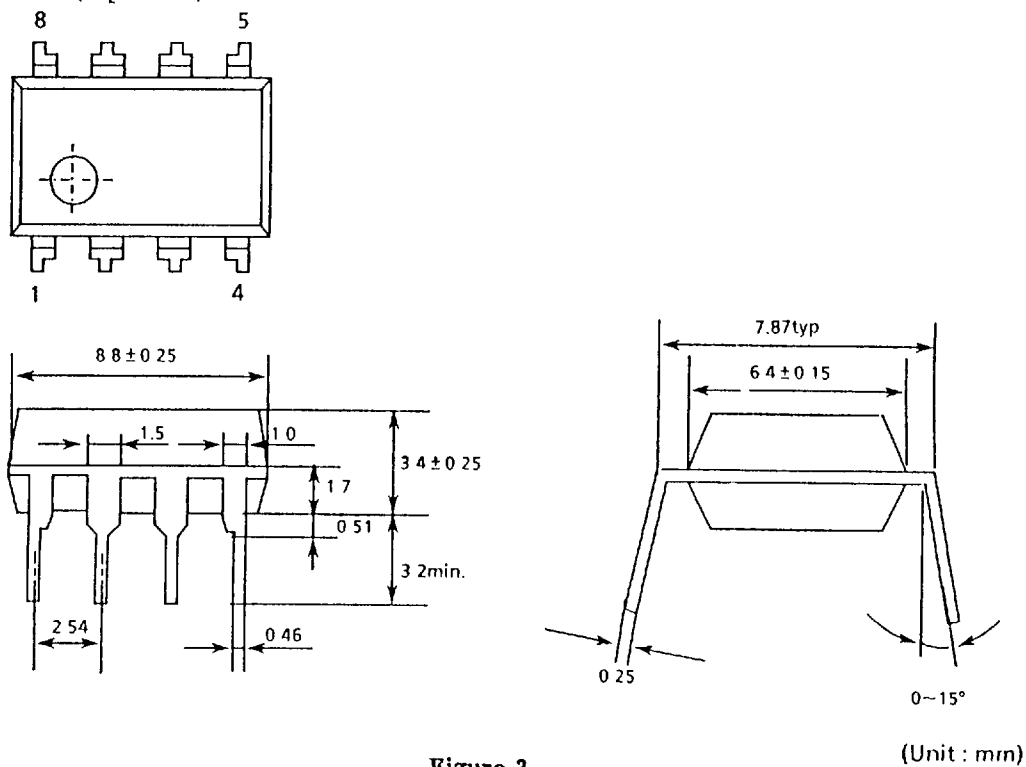


Figure 3

2. S-2100RF (8-pin SOP)

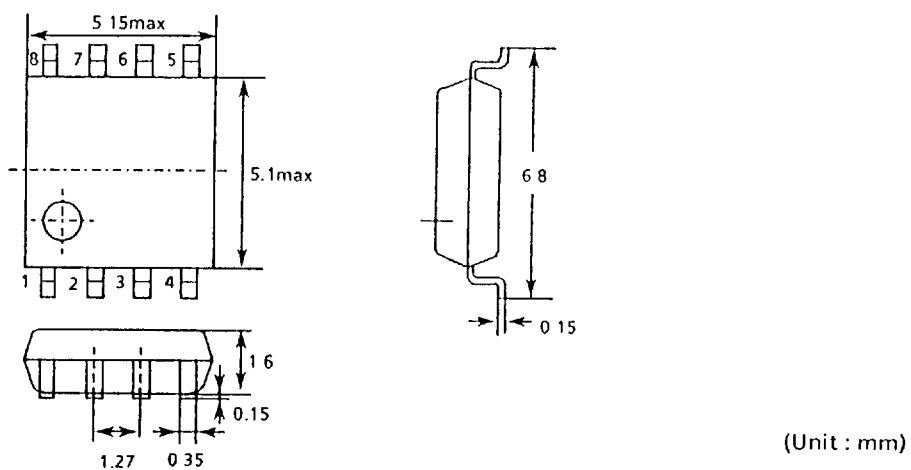


Figure 4

# S-2100R

## Read Mode Timing Chart $\overline{PD}/V_{pp}=GND$

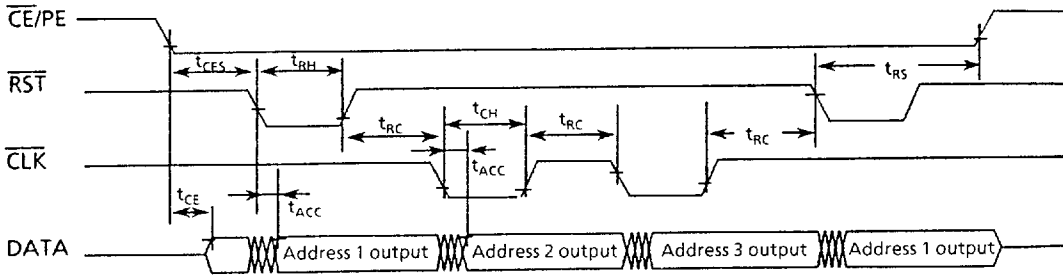


Figure 5

## Counter Hold Mode Timing Chart $\overline{PD}/V_{pp}=GND$

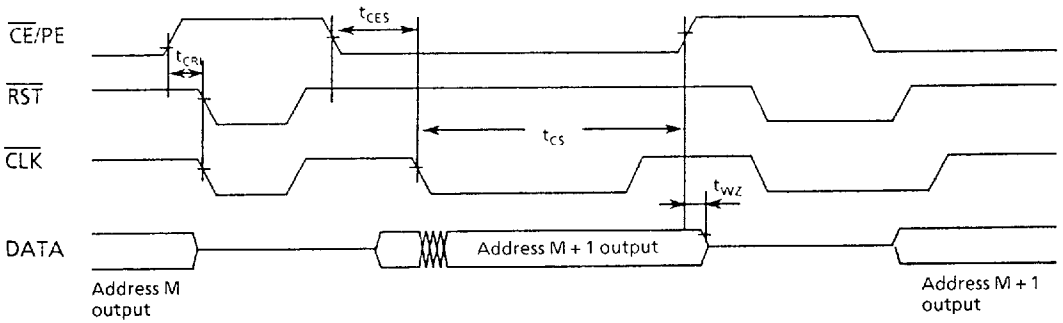


Figure 6

## Write Mode Timing Chart

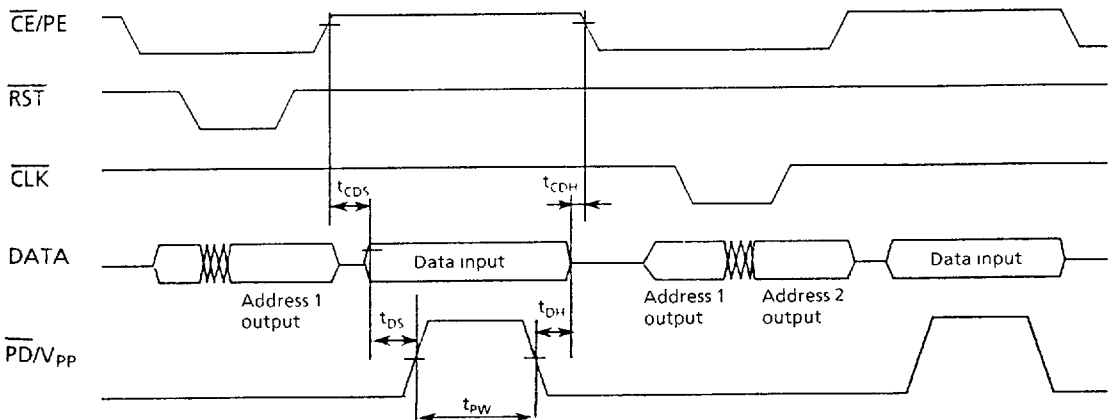
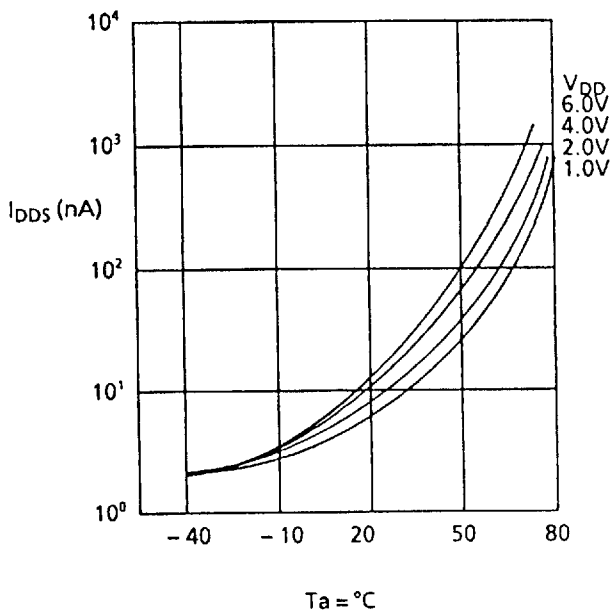


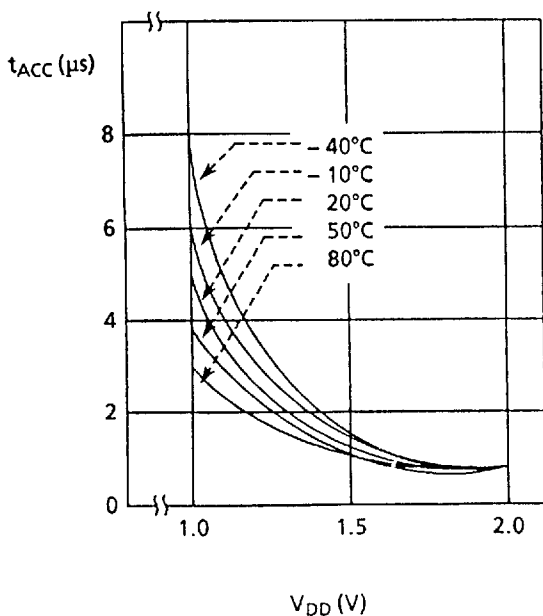
Figure 7

■ Characteristics

- Standby current consumption ( $I_{DDs}$ )  
– Ambient temperature ( $T_a$ )



- Access time ( $t_{ACC}$ )  
– Power supply voltage ( $V_{DD}$ )



- Access time ( $t_{ACC}$ )  
– Power supply voltage ( $V_{DD}$ )

